METHOD OF MANUFACTURING 3-D SPIRAL STACKED INDUCTOR ON SEMICONDUCTOR MATERIAL

ABSTRACT

A method of manufacturing a 3-D spiral stacked inductor is provided having a substrate with a plurality of turns in a plurality of levels wherein the number of levels increases from an inner turn to the outer turn of the inductor. First and second connecting portions are respectively connected to an inner turn and an outermost turn, and a dielectric material contains the first and second connecting portions and the plurality of turns over the substrate.

FIG. 4